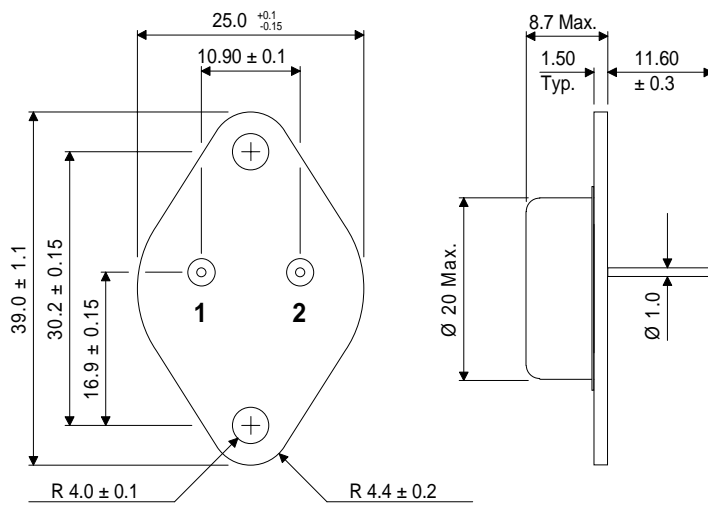


**BUZ902D**  
**BUZ903D**

## MECHANICAL DATA

Dimensions in mm



**TO-3**

Pin 1 – Gate

Pin 2 – Drain

Case – Source

www.DataSheet4U.com

## N-CHANNEL POWER MOSFET

### POWER MOSFETS FOR AUDIO APPLICATIONS

#### FEATURES

- HIGH SPEED SWITCHING
- SEMEFAB DESIGNED AND DIFFUSED
- HIGH VOLTAGE (220V & 250V)
- HIGH ENERGY RATING
- ENHANCEMENT MODE
- INTEGRAL PROTECTION DIODES
- COMPLIMENTARY P-CHANNEL BUZ907D & BUZ908D

#### ABSOLUTE MAXIMUM RATINGS

( $T_{case} = 25^{\circ}C$  unless otherwise stated)

		<b>BUZ902D</b>	<b>BUZ903D</b>
$V_{DSX}$	Drain – Source Voltage	220V	250V
$V_{GSS}$	Gate – Source Voltage	±14V	
$I_D$	Continuous Drain Current	16A	
$I_{D(PK)}$	Body Drain Diode	16A	
$P_D$	Total Power Dissipation @ $T_{case} = 25^{\circ}C$	250W	
$T_{stg}$	Storage Temperature Range	-55 to 150°C	
$T_j$	Maximum Operating Junction Temperature	150°C	
$R_{\theta JC}$	Thermal Resistance Junction – Case	0.5°C/W	

**STATIC CHARACTERISTICS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
BV <sub>DSX</sub> Drain – Source Breakdown Voltage	V <sub>GS</sub> = -10V I <sub>D</sub> = 10mA	BUZ902D	220			V
		BUZ903D	250			V
BV <sub>GSS</sub> Gate – Source Breakdown Voltage	V <sub>DS</sub> = 0	I <sub>G</sub> = ±100µA	±14			V
V <sub>GS(OFF)</sub> Gate – Source Cut-Off Voltage	V <sub>DS</sub> = 10V	I <sub>D</sub> = 100mA	0.10		1.5	V
V <sub>DS(SAT)</sub> * Drain – Source Saturation Voltage	V <sub>GD</sub> = 0	I <sub>D</sub> = 16A			12	V
R <sub>DS(on)</sub> * Static – Source Resistance	V <sub>GS</sub> = 10	I <sub>D</sub> = 16A			0.75	Ω
I <sub>DSX</sub> Drain – Source Cut-Off Current	V <sub>GS</sub> = -10V	V <sub>DS</sub> = 220V BUZ902D			10	mA
		V <sub>DS</sub> = 250V BUZ903D			10	mA
y <sub>fs</sub> * Forward Transfer Admittance	V <sub>DS</sub> = 10V	I <sub>D</sub> = 3A	1.4		4	S

**DYNAMIC CHARACTERISTICS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
C <sub>iSS</sub> Input Capacitance	V <sub>DS</sub> = 10V f = 1MHz			TBA		pF
C <sub>oss</sub> Output Capacitance				TBA		
C <sub>rSS</sub> Reverse Transfer Capacitance				TBA		
t <sub>on</sub> Turn-on Time	V <sub>DS</sub> = 20V			TBA		ns
t <sub>off</sub> Turn-off Time	I <sub>D</sub> = 7A			TBA		

\* Pulse Test: Pulse Width = 300µs , Duty Cycle ≤ 2%.

